

Description

The VST06N031 uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

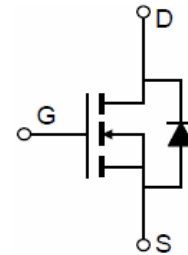
- $V_{DS} = 60V, I_D = 150A$
 $R_{DS(ON)} < 3.4m\Omega @ V_{GS}=10V$ (Typ:3.1m Ω)
- Excellent gate charge x $R_{DS(on)}$ product
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



TO-252



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
VST06N031-T2	VST06N031	TO-252	-	-	-

Absolute Maximum Ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous (Silicon Limited)	I_D	150	A
Drain Current-Continuous($T_C=100^\circ\text{C}$)	$I_D(100^\circ\text{C})$	110	A
Pulsed Drain Current	I_{DM}	600	A
Maximum Power Dissipation	P_D	180	W
Derating factor		1.2	W/ $^\circ\text{C}$
Single pulse avalanche energy ^(Note 5)	E_{AS}	800	mJ
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

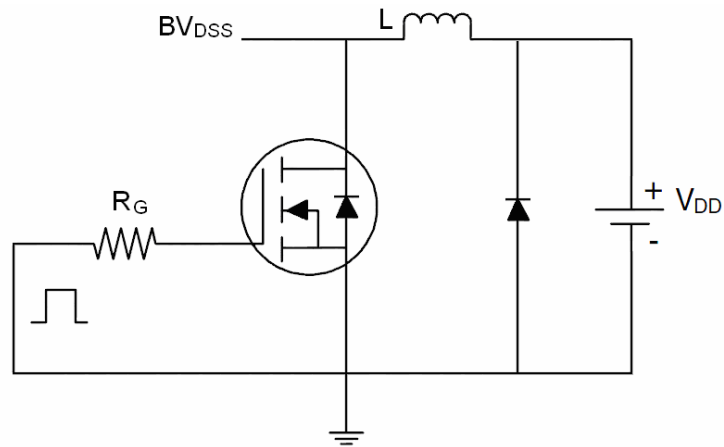
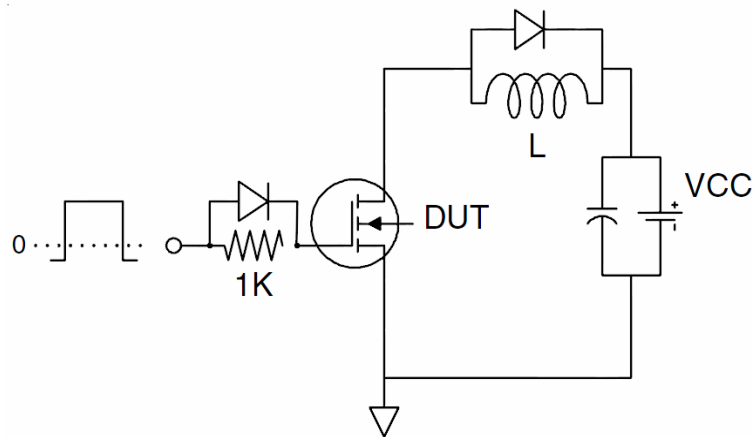
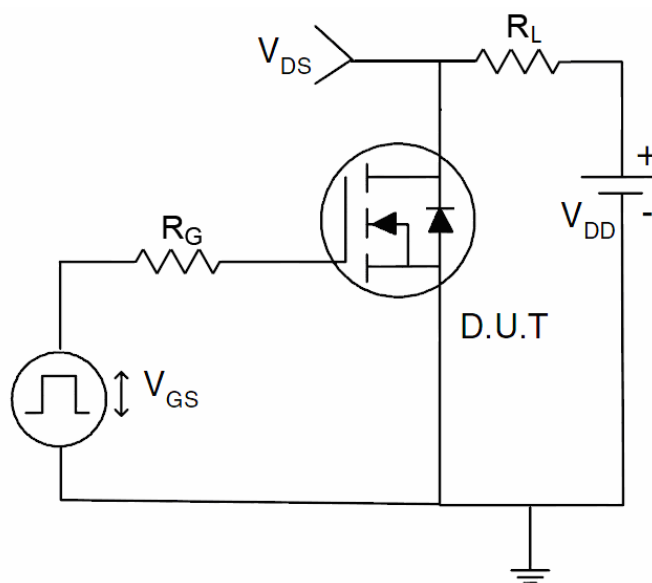
Thermal Resistance, Junction-to-Case ^(Note 2)	$R_{\theta JC}$	0.83	$^{\circ}\text{C}/\text{W}$
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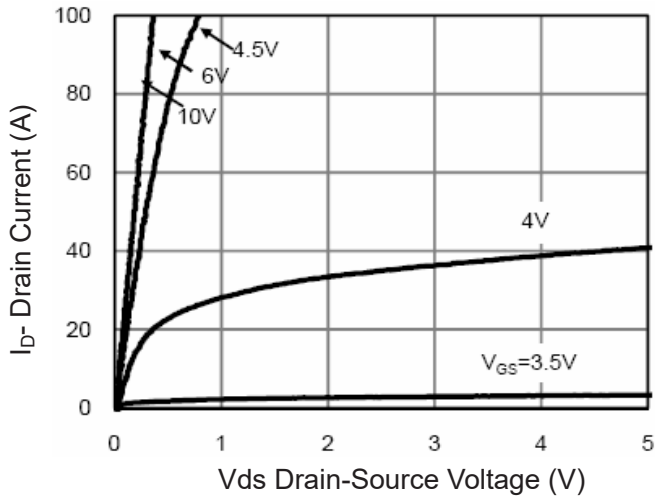
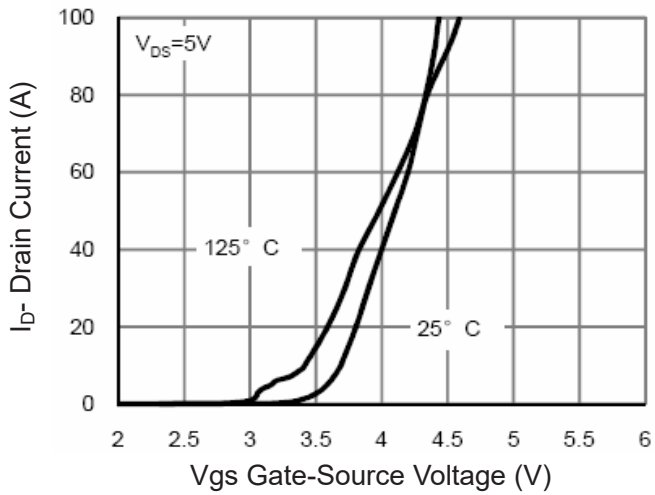
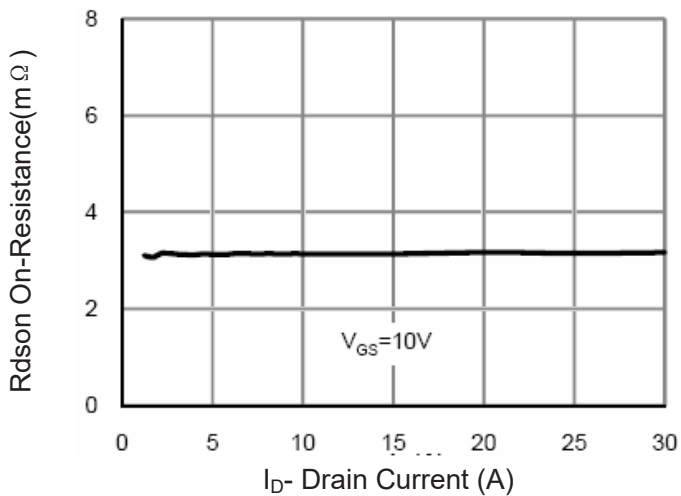
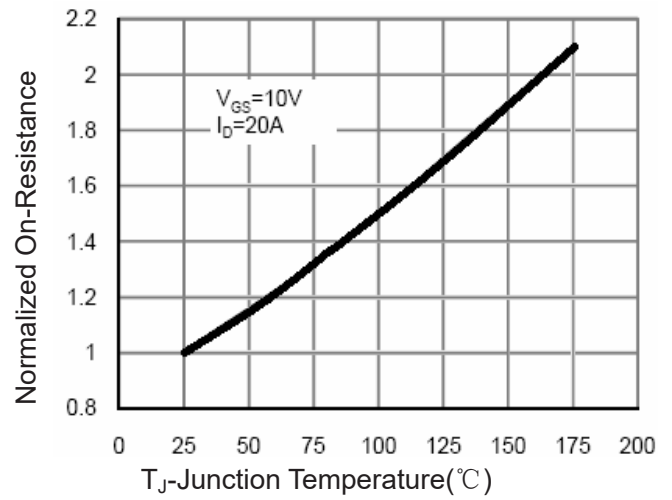
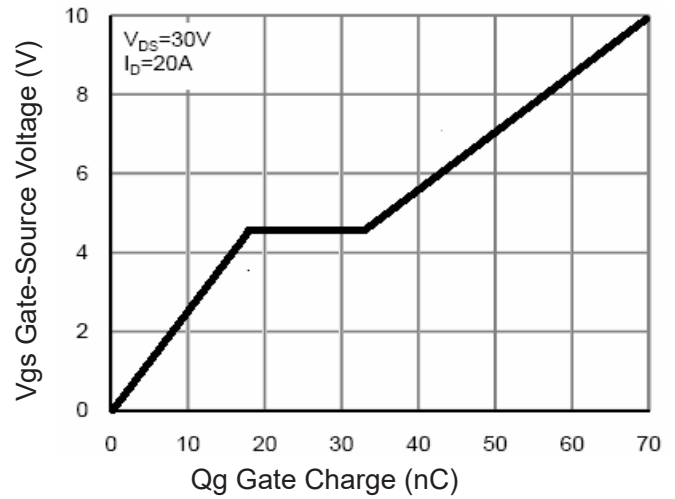
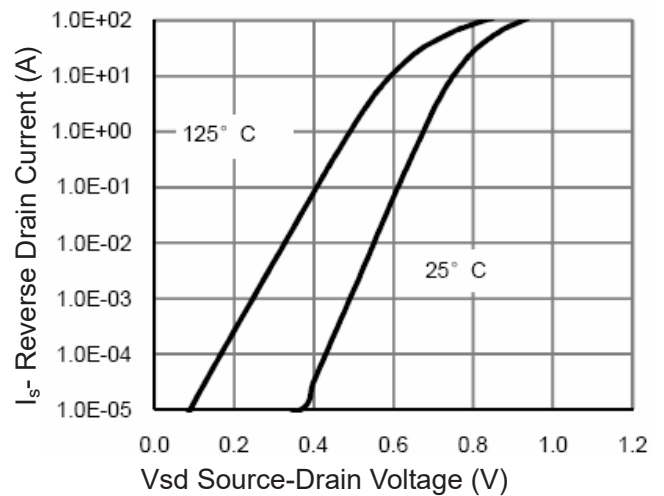
Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

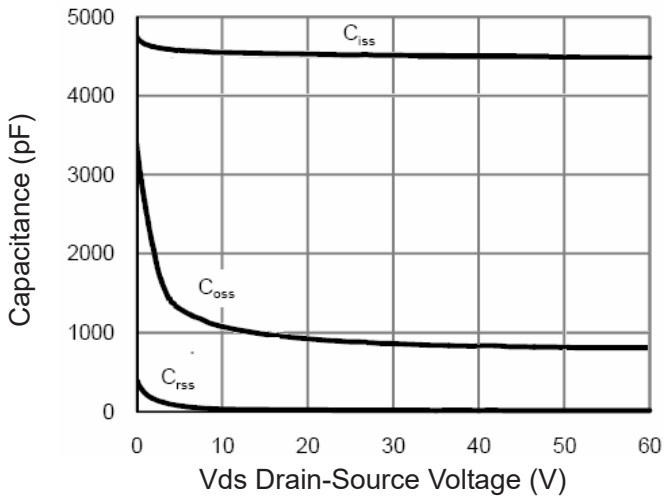
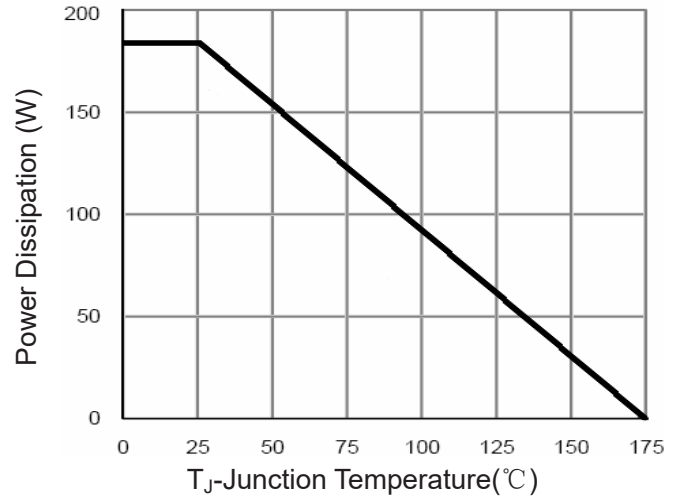
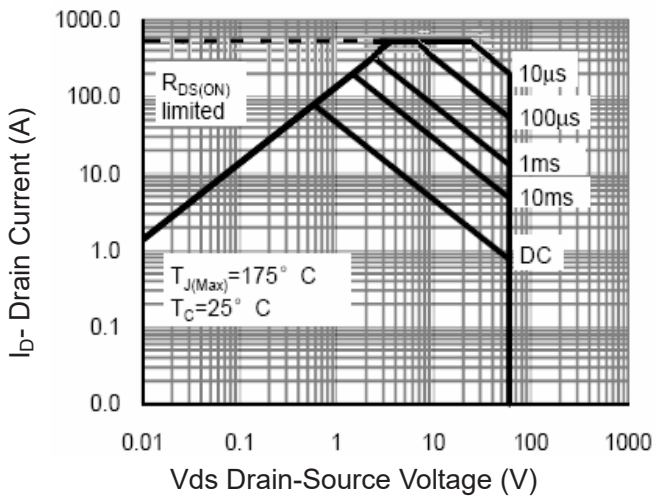
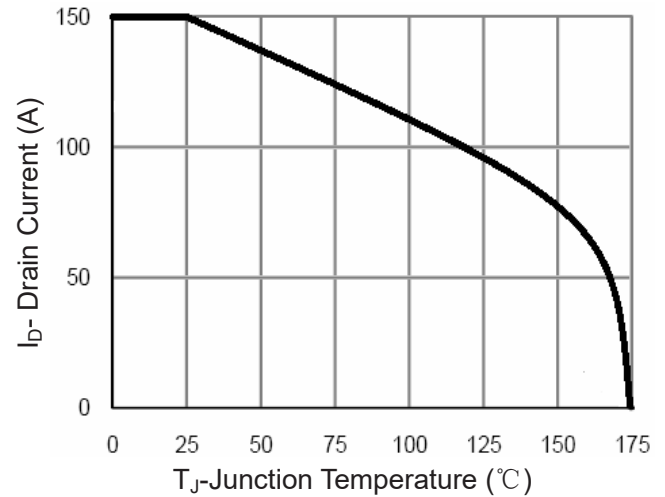
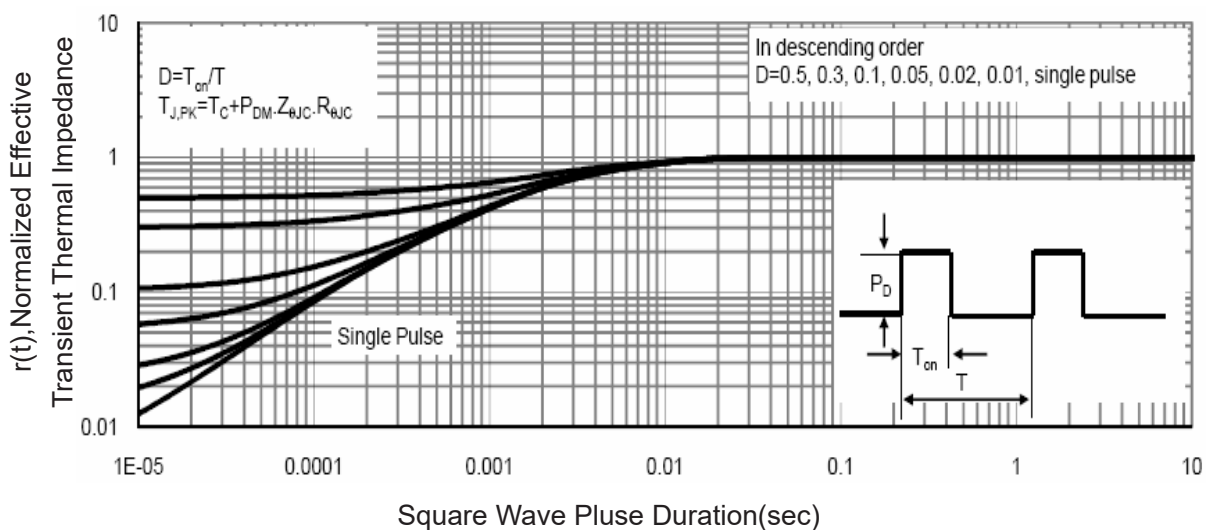
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60		-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2	2.8	4	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=20A$	-	3.1	3.4	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=20A$	-	60	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C_{iss}	$V_{DS}=30V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	4500	-	PF
Output Capacitance	C_{oss}		-	965	-	PF
Reverse Transfer Capacitance	C_{rss}		-	24.2	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=30V, I_D=20A$ $V_{GS}=10V, R_G=4.7\Omega$	-	21	-	nS
Turn-on Rise Time	t_r		-	20	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	36	-	nS
Turn-Off Fall Time	t_f		-	6	-	nS
Total Gate Charge	Q_g	$V_{DS}=30V, I_D=20A,$ $V_{GS}=10V$	-	70		nC
Gate-Source Charge	Q_{gs}		-	18.6		nC
Gate-Drain Charge	Q_{gd}		-	15.3		nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V_{SD}	$V_{GS}=0V, I_S=20A$	-		1.2	V
Diode Forward Current ^(Note 2)	I_S		-	-	150	A
Reverse Recovery Time	t_{rr}	$T_J = 25^{\circ}\text{C}, I_F = I_S$ $di/dt = 100A/\mu\text{s}$ ^(Note 3)	-	50		nS
Reverse Recovery Charge	Q_{rr}		-	66		nC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=30V, V_G=10V, L=0.5\text{mH}, R_g=25\Omega$

Test Circuit
1) E_{AS} test Circuit

2) Gate charge test Circuit

3) Switch Time Test Circuit


Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

Figure 2 Transfer Characteristics

Figure 3 Rdson- Drain Current

Figure 4 Rdson-Junction Temperature

Figure 5 Gate Charge

Figure 6 Source- Drain Diode Forward


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating

Figure 8 Safe Operation Area

Figure 10 Current De-rating

Figure 11 Normalized Maximum Transient Thermal Impedance